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PAGE 2

YO998426DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Chan et al.

Serial No. 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

or: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER BONDING TECHNIQUES

Commissioner For Patents
Alexandria, VA 22313-1450

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action mailed February 12, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please cancel claim 24 without prejudice or disclaimer.

Please amend the remaining claims as follows:

CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)

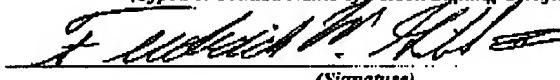
Applicant(s): Chan et al.

Docket No.

YO998-426DIV

Serial No.
10/051,562Filing Date
January 18, 2002Examiner
C. NovacekGroup Art Unit
2822**Invention: SELF-ALIGNED DOUBLE GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER
BONDING TECHNIQUES**

I hereby certify that this

Amendment Under 37 CFR 1.111*(Identify type of correspondence)*is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. 703-872-9318)on May 9, 2003
*(Date)***Frederick W. Gibb, III***(Typed or Printed Name of Person Signing Certificate)**(Signature)***Note: Each paper must have its own certificate of mailing.****FAX RECEIVED**

MAY 09 2003

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